

PSMN022-30PL

N-channel 30 V 22 mΩ logic level MOSFET Rev. 02 — 1 November 2010

Product data sheet

Product profile 1.

1.1 General description

Logic level N-channel MOSFET in TO220 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for logic level gate drive sources

1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	30	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u>	-	-	30	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see Figure 2	-	-	41	W
Tj	junction temperature		-55	-	175	°C
Static cha	racteristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 5 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 13}{\text{ Figure } 13}$	-	27	34	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 13}}{\text{Figure 13}}$	-	19	22	mΩ
Dynamic o	characteristics					
Q_{GD}	gate-drain charge	$V_{GS} = 4.5 \text{ V}; I_D = 5 \text{ A};$	-	1.4	-	nC
Q _{G(tot)}	total gate charge	V _{DS} = 15 V; see <u>Figure 14;</u> see <u>Figure 15</u>	-	4.4	-	nC
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\begin{split} &V_{GS} = 10 \text{ V; } T_{j(\text{init})} = 25 \text{ °C;} \\ &I_D = 30 \text{ A; } V_{\text{sup}} \leq 30 \text{ V;} \\ &R_{GS} = 50 \Omega; \text{ unclamped} \end{split}$	-	-	7	mJ



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain	mb	D
3	S	source		G (EX)
mb	D	mounting base; connected to drain	1 2 3	mbb076 S
			SOT78 (TO-220AB)	

3. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PSMN022-30PL	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78		

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	30	V
V_{DGR}	drain-gate voltage	$T_j \ge 25$ °C; $T_j \le 175$ °C; $R_{GS} = 20$ kΩ	-	30	V
V_{GS}	gate-source voltage		-20	20	V
I _D	drain current	$V_{GS} = 10 \text{ V; } T_{mb} = 100 \text{ °C; see } \frac{\text{Figure 1}}{\text{Model}}$	-	22	Α
		$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	-	30	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 \text{ °C}$; see Figure 3	-	125	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	41	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drain	diode				
Is	source current	T _{mb} = 25 °C	-	30	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	125	Α
Avalanche rug	ggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 30 A; V_{sup} ≤ 30 V; R_{GS} = 50 Ω ; unclamped	-	7	mJ

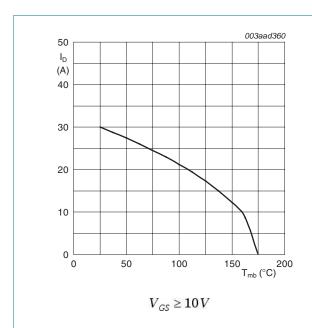
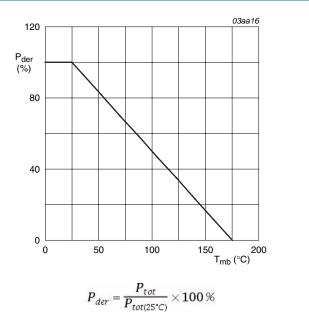


Fig 1. Continuous drain current as a function of mounting base temperature



 Normalized total power dissipation as a function of mounting base temperature

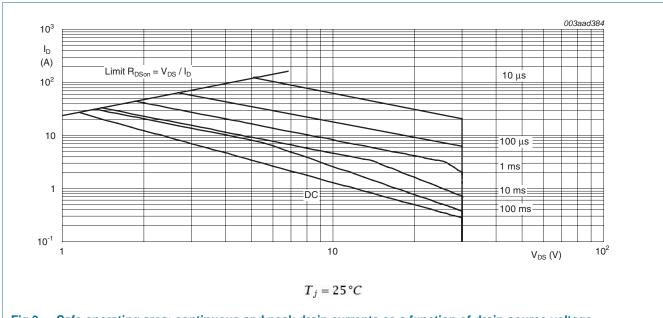


Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	3.1	3.6	K/W

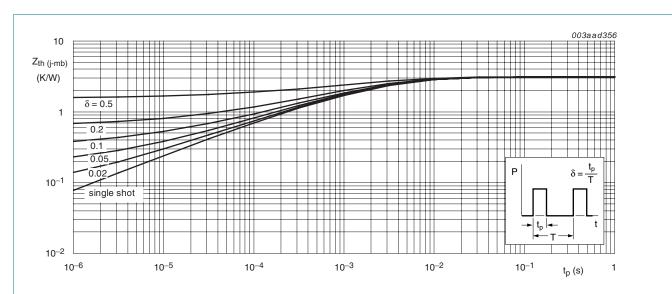


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

6. Characteristics

Table 6. Characteristics

$\begin{tabular}{ll} Symbol & Parameter & Conditions \\ Static characteristics \\ $V_{(BR)DSS}$ & drain-source breakdown & $I_D=250~\mu A;~V_{GS}=0~V;~T_j=25$ \\ \end{tabular}$		Тур	Max	Unit
$V_{(BR)DSS}$ drain-source breakdown $I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25$				
	5 °C 27	-	-	V
voltage $I_D = 250 \mu\text{A}; V_{GS} = 0 V; T_j = -55$		-	-	V
$V_{GS(th)}$ gate-source threshold voltage $I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 25$ ° see Figure 10; see Figure 11	C; 1.3	1.7	2.15	V
$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 175$ see Figure 11	°C; 0.5	-	-	V
$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ see}$ see Figure 11	°C; -	-	2.45	V
I_{DSS} drain leakage current $V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ C}$	°C -	0.3	1	μΑ
$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ V}$	5 °C -	-	50	μΑ
I_{GSS} gate leakage current $V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ C}$	°C -	10	100	nΑ
$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25$	°C -	10	100	nΑ
R_{DSon} drain-source on-state $V_{GS} = 4.5 \text{ V}; I_D = 5 \text{ A}; T_j = 175 \text{ G}$ resistance see Figure 12	°C; -	-	64.6	mΩ
$V_{GS} = 4.5 \text{ V}; I_D = 5 \text{ A}; T_j = 25 ^{\circ}\text{C}$ see Figure 13	C; -	27	34	mΩ
$V_{GS} = 10 \text{ V; } I_D = 5 \text{ A; } T_j = 175 ^{\circ}$ see Figure 12	°C; -	35	41.8	mΩ
$V_{GS} = 10 \text{ V; } I_D = 5 \text{ A; } T_j = 100 ^{\circ}$ see Figure 12	°C; -	-	31	mΩ
$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 25 ^{\circ}\text{C}$ see Figure 13	-	19	22	mΩ
R_G gate resistance $f = 1 \text{ MHz}$	-	2	-	Ω
Dynamic characteristics				
$Q_{G(tot)}$ total gate charge $I_D = 5 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 10 \text{ see } \frac{\text{Figure 15}}{\text{Figure 15}}$	V; -	9	-	nC
$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	8	-	nC
$I_D = 5 \text{ A}$; $V_{DS} = 15 \text{ V}$; $V_{GS} = 4.5 \text{ V}$. V; -	4.4	-	nC
Q _{GS} gate-source charge see Figure 14; see Figure 15	-	1.6	-	nC
$Q_{GS(th)}$ pre-threshold gate-source $I_D = 5 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ charge}$ see Figure 14		8.0	-	nC
Q _{GS(th-pl)} post-threshold gate-source charge	-	0.8	-	nC
Q_{GD} gate-drain charge $I_D = 5 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5$ see Figure 14; see Figure 15		1.4	-	nC
$V_{GS(pl)}$ gate-source plateau voltage $V_{DS} = 15 \text{ V}$; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	3	-	V
C_{iss} input capacitance $V_{DS} = 15 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MH}$	Hz; -	447	-	pF
C_{oss} output capacitance $T_j = 25$ °C; see Figure 16	-	96	-	pF
C _{rss} reverse transfer capacitance	-	61	-	pF

 Table 6.
 Characteristics ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t _{d(on)}	turn-on delay time	V_{DS} = 15 V; R_{L} = 1.5 Ω ; V_{GS} = 4.5 V; $R_{G(ext)}$ = 4.7 Ω	-	12	-	ns
t _r	rise time		-	29	-	ns
t _{d(off)}	turn-off delay time		-	17	-	ns
t _f	fall time		-	7	-	ns
Source-dra	in diode					
V_{SD}	source-drain voltage	$I_S = 5 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; see Figure 17	-	0.7	1.2	V
t _{rr}	reverse recovery time	$I_S = 5 \text{ A}$; $dI_S/dt = -100 \text{ A/}\mu\text{s}$;	-	22	-	ns
Q _r	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 20 \text{ V}$	-	10	-	nC

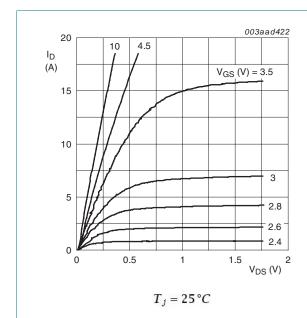


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

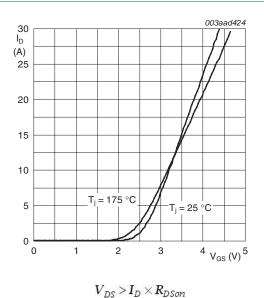


Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

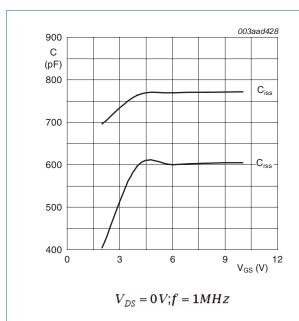


Fig 7. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

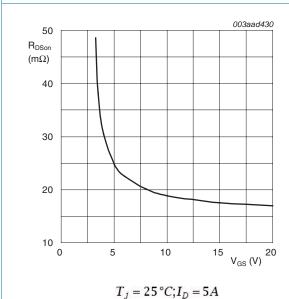


Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

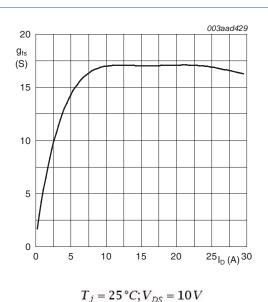
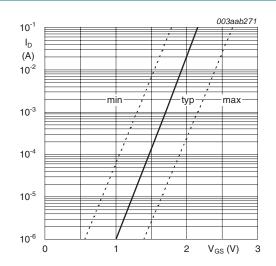


Fig 8. Forward transconductance as a function of drain current; typical values



 $T_j = 25 \,{}^{\circ}C; V_{DS} = 5V$

Fig 10. Sub-threshold drain current as a function of gate-source voltage

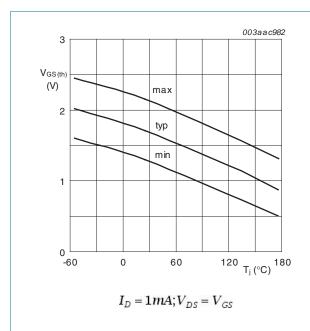


Fig 11. Gate-source threshold voltage as a function of junction temperature

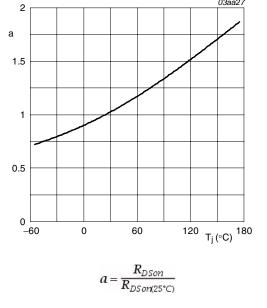


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

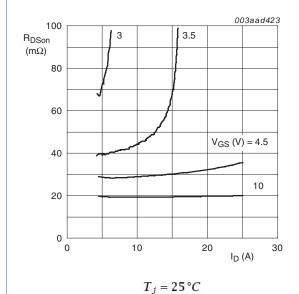


Fig 13. Drain-source on-state resistance as a function of drain current; typical values

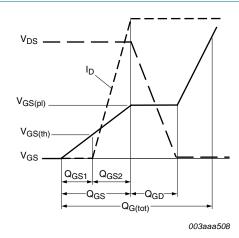


Fig 14. Gate charge waveform definitions

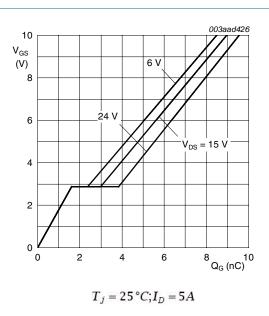
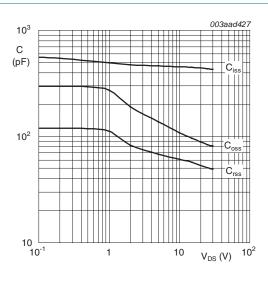
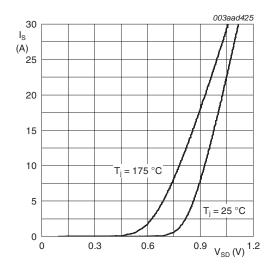


Fig 15. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0V; f = 1MHz$

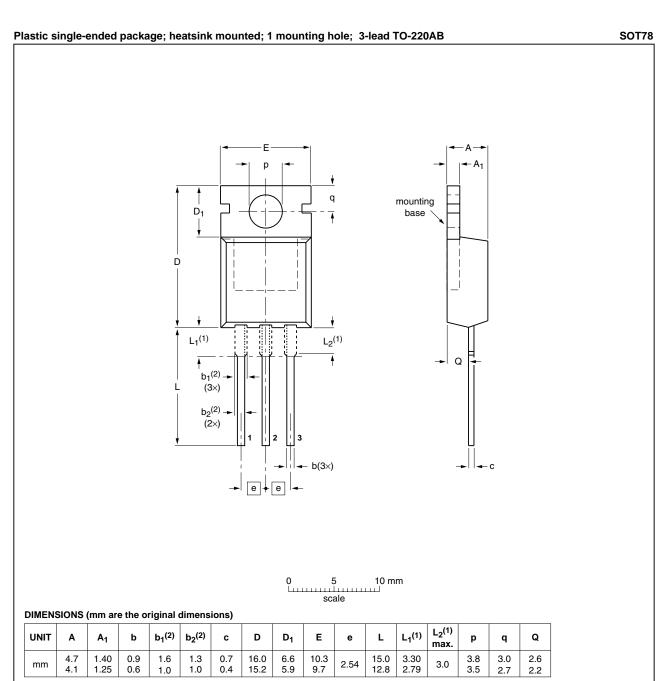
Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



 $V_{GS} = 0V$

Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline



Notes

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE	REF		REFERENCES			ISSUE DATE
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT78		3-lead TO-220AB	SC-46			08-04-23 08-06-13

Fig 18. Package outline SOT78 (TO-220AB)

PSMN022-30PL

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN022-30PL v.2	20101101	Product data sheet	-	PSMN022-30PL v.1
Modifications:	 Various change 	es to content.		
PSMN022-30PL v.1	20101018	Product data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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N-channel 30 V 22 mΩ logic level MOSFET

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